

L Number	Hits	Search Text	DB	Time stamp
-	20	((atomic adj layer) adj (deposition or epitaxy)) and (surface same terminat\$4)	USPAT	2002/05/30 12:20
-	100	((atomic adj layer) adj (deposition or epitaxy)) and ((metal adj oxide) or alumina or (aluminum with oxide))	USPAT	2001/02/16 14:56
-	57	((atomic adj layer) adj (deposition or epitaxy)) and ((metal adj oxide) or alumina or (aluminum with oxide))) and oxygen	USPAT	2001/02/16 14:51
-	6	"3306678"	USPAT	2001/02/16 14:52
-	70	"3306768"	USPAT	2001/02/16 14:52
-	15	((atomic adj layer) adj (deposition or epitaxy)) and (reactants same order)	USPAT	2001/02/21 10:56
-	2	((atomic adj layer) adj (deposition or epitaxy)) and (oxygen with (purge or purged or purging))	USPAT	2001/02/21 15:01
-	402	(117/95,950).CCLS.	USPAT	2001/02/21 11:00
-	41	((("117/95,950").CCLS.) and (surface same terminat\$4)	USPAT	2001/02/21 13:57
-	3	((("117/95,950").CCLS.) and ((surface same terminat\$4) same oxygen)	USPAT	2001/02/21 11:43
-	2	((("117/95,950").CCLS.) and (terminat\$4 with oxygen)	USPAT	2001/02/21 11:25
-	1	((atomic adj layer) adj (deposition or epitaxy)) and (oxygen with (terminat\$4))	USPAT	2001/02/21 11:42
-	988	((surface same terminat\$4) same oxygen)	USPAT	2001/02/21 11:46
-	67	((surface same terminat\$4) same oxygen) same bonds	USPAT	2001/02/21 11:53
-	2	"5039626"	USPAT	2001/02/21 14:59
-	0	((atomic adj layer) adj (deposition or epitaxy)) and (oxygen with (flush or flushed or flushing))	USPAT	2001/02/21 15:04
-	85	substrate same (oxygen with (flush or flushed or flushing))	USPAT	2001/02/21 15:09
-	2	(((((atomic adj layer) adj (deposition or epitaxy)) or ald or ale) same (nitride or nitrides)) and (purge with (nitrogen or "N.sub.2"))	USPAT	2001/12/20 14:36
-	42	(((((atomic adj layer) adj (deposition or epitaxy)) or ald or ale) same (nitride or nitrides))	USPAT	2001/12/20 15:06
-	26	(((((atomic adj layer) adj (deposition or epitaxy)) or ald or ale) same (nitride or nitrides))) and ((substrate or substrates) with silicon)	USPAT	2001/12/20 15:39
-	212	427/255.32	USPAT	2001/12/20 15:40
-	189	((flowing or flushing) same oxygen) and silicon and (surface same terminat\$4)	USPAT	2002/05/30 12:23
-	5	((flowing or flushing) same oxygen) same (repeated or twice)) and silicon and (surface same terminat\$4)	USPAT	2002/05/30 12:22
-	58	((flowing or flushing) same oxygen) same (surface same terminat\$4)	USPAT	2002/05/30 12:36
-	122	((flowing or flushing) same oxygen) same (surface same activat\$4)	USPAT	2002/05/30 12:38
-	639	((flowing or flushing) same oxygen) same (activat\$4)	USPAT	2002/05/30 12:37
-	136	((flowing or flushing) same oxygen) same (activat\$4)) and silicon	USPAT; US-PGPUB	2002/05/30 12:37
-	29	((flowing or flushing) same oxygen) same (surface same activat\$4)) and (((flowing or flushing) same oxygen) same (activat\$4)) and silicon)	USPAT	2002/05/30 12:43
-	12	((flowing or flushing) same oxygen) same (surface near3 activat\$4)	USPAT	2002/05/30 12:39
-	777	(oxygen) same (surface near3 activat\$4)	USPAT	2002/05/30 12:39
-	8	(((((flowing or flushing) same oxygen) same (surface same activat\$4)) and (((flowing or flushing) same oxygen) same (activat\$4)) and silicon)) and (twice or repeated)	USPAT	2002/05/30 12:44
-	288	((oxygen) same (surface near3 activat\$4)) and (twice or repeated)	USPAT	2002/05/30 12:44

-	10	((oxygen) same (surface near3 activat\$4))	USPAT	2002/05/30 12:44
-	2965	semiconductor and ((oxidi\$8 or oxidation or oxide) same temperature same "300")	USPAT	2002/11/05 16:47
-	1434	semiconductor and (oxygen same temperature same "300")	USPAT	2002/11/05 16:47
-	900	(semiconductor and ((oxidi\$8 or oxidation or oxide) same temperature same "300")) and (semiconductor and (oxygen same temperature same "300"))	USPAT	2002/11/05 16:47
-	459	semiconductor and ((oxidi\$8 or oxidation or oxide) with temperature with "300")	USPAT	2002/11/05 16:49
-	179	semiconductor and ((oxidi\$8 or oxidation or oxide) with temperature with "300" with silicon!)	USPAT	2002/11/05 16:50
-	2	((("6473564") or ("6275649"))).PN.	USPAT; US-PGPUB	2002/11/06 16:44
-	3	((("5169579") or ("4806996") or ("5851849"))).PN.	USPAT; US-PGPUB	2004/04/13 20:35
-	1	("5433902").PN.	USPAT; US-PGPUB	2004/04/13 20:39
-	1	("6203613").PN.	USPAT; US-PGPUB	2004/04/30 14:16
-	1	("6342277").PN.	USPAT; US-PGPUB	2004/04/30 14:11
-	7	((("6586056") or ("6540838") or ("6391785") or ("6305314") or ("3203613") or ("6200893") or ("5281274"))).PN.	USPAT; US-PGPUB	2004/04/30 14:21
-	5	((("6586056") or ("6540838") or ("6391785") or ("6305314") or ("3203613") or ("6200893") or ("5281274"))).PN.) and terminat\$	USPAT; US-PGPUB	2004/04/30 14:43
-	246	(atomic adj layer adj (deposit\$6 or epitax\$6)) and (sequence same (precursor or reactant or coreactant or co-reactant))	USPAT; US-PGPUB	2004/04/30 16:02
-	231	((atomic adj layer adj (deposit\$6 or epitax\$6)) and (sequence same (precursor or reactant or coreactant or co-reactant))) and (oxide or nitride)	USPAT; US-PGPUB	2004/04/30 14:47
-	370	(atomic adj layer adj (deposit\$6 or epitax\$6)) and (surface with terminat\$)	USPAT; US-PGPUB	2004/04/30 17:12
-	150	(atomic adj layer adj (deposit\$6 or epitax\$6)) and (first near3 (oxygen or water or nitrogen))	USPAT; US-PGPUB	2004/04/30 16:21
-	0	(atomic adj layer adj (deposit\$6 or epitax\$6)) and (order with (reactants! OR PRECURSORS!) with (important or critical or unimportant))	USPAT; US-PGPUB	2004/04/30 16:22
-	72	(atomic adj layer adj (deposit\$6 or epitax\$6)) and (order with (important or critical or unimportant))	USPAT; US-PGPUB	2004/04/30 16:29
-	35	(atomic adj layer adj (deposit\$6 or epitax\$6)) and (first near3 (important or critical or unimportant))	USPAT; US-PGPUB	2004/04/30 16:30
-	0	(atomic adj layer adj (deposit\$6 or epitax\$6)) and ((first near3 (reactant or precursor)) with (important or critical or unimportant))	USPAT; US-PGPUB	2004/04/30 16:32
-	7	(atomic adj layer adj (deposit\$6 or epitax\$6)) and (gates.in. or neumayer.in.)	USPAT; US-PGPUB	2004/04/30 16:34
-	33	(atomic adj layer adj (deposit\$6 or epitax\$6)) and (pulse near2 sequence)	USPAT; US-PGPUB	2004/04/30 16:41
-	57	(atomic adj layer adj (deposit\$6 or epitax\$6) or ALD or ALE) and sequence	EPO; JPO; DERWENT; IBM_TDB	2004/04/30 16:57
-	0	(atomic adj layer adj (deposit\$6 or epitax\$6) or ALD or ALE) and ("TiCL.sub.4" or (titanium! adj tetrachloride)) and (ammonia! or "NH.sub.3") and (silicon! with substrate)	EPO; JPO; DERWENT; IBM_TDB	2004/04/30 16:59

-	1	((atomic adj layer adj (deposit\$6 or epitax\$6) or ALD or ALE) and ((titanium adj nitride) or (TiN with SiN)) and (silicon! with substrate))	EPO; JPO; DERWENT; IBM_TDB	2004/04/30 17:07
-	120	((atomic adj layer adj (deposit\$6 or epitax\$6) or ALD or ALE) and ("TiCL.sub.4" or (titanium! adj tetrachloride)) and (ammonia! or "NH.sub.3") and (silicon! with substrate))	USPAT; US-PGPUB	2004/04/30 17:03
-	65	((atomic adj layer adj (deposit\$6 or epitax\$6) or ALD or ALE) and ("TiCL.sub.4" or (titanium! adj tetrachloride)) and (ammonia! or "NH.sub.3") and (silicon! with substrate)) and ((atomic adj layer adj (deposit\$6 or epitax\$6) or ALD or ALE) and ((titanium adj nitride) or (TiN with SiN)) and (silicon! with substrate))	USPAT; US-PGPUB	2004/05/02 21:04
-	74	((atomic adj layer adj (deposit\$6 or epitax\$6) or ALD or ALE) and ((titanium adj nitride) or (TiN with SiN)) and (silicon! with substrate)) and ("TiCL.sub.4" or (titanium! adj tetrachloride))	USPAT; US-PGPUB	2004/04/30 17:06
-	348	((atomic adj layer adj (deposit\$6 or epitax\$6) or ALD or ALE) and ((titanium adj nitride) or (TiN with SiN)) and (silicon! with substrate))	USPAT; US-PGPUB	2004/04/30 17:06
-	749	((atomic adj layer adj (deposit\$6 or epitax\$6) or ALD or ALE) same nitride	USPAT; US-PGPUB	2004/05/02 21:02
-	156	((atomic adj layer adj (deposit\$6 or epitax\$6) or ALD or ALE) same nitride) and ("TiCL.sub.4" or (titanium! adj tetrachloride))	USPAT; US-PGPUB	2004/04/30 17:12
-	0	((atomic adj layer adj (deposit\$6 or epitax\$6) or ALD or ALE) same nitride) and (silicon! with substrate)	EPO; JPO; DERWENT; IBM_TDB	2004/04/30 17:07
-	0	((atomic adj layer adj (deposit\$6 or epitax\$6)) and ((reactant or precursor) adj5 purge adj5 (reactant or precursor) adj5 purge)	USPAT; US-PGPUB	2004/04/30 17:13
-	0	((atomic adj layer adj (deposit\$6 or epitax\$6)) and ((source) adj5 purge adj5 (source) adj5 purge)	USPAT; US-PGPUB	2004/05/02 19:49
-	52	((atomic adj layer adj (deposit\$6 or epitax\$6)) and (sequence with (reactant or precursor or source) with purge)	USPAT; US-PGPUB	2004/04/30 17:16
-	103	((terminat\$ with surface with (silicon) with (oxygen or nitrogen))	USPAT; US-PGPUB	2004/04/30 17:17
-	90330	("427").CLAS.	USPAT; US-PGPUB	2004/04/30 17:17
-	4	((terminat\$ with surface with (silicon) with (oxygen or nitrogen))) and (("427").CLAS.)	USPAT; US-PGPUB	2004/04/30 17:17
-	6	((atomic adj layer adj (deposit\$6 or epitax\$6) or ALD or ALE) and ((alumina or ("Al.sub.2" adj "O.sub.3")) same (oxygen near5 water))	USPAT; US-PGPUB	2004/05/02 15:20
-	115	((atomic adj layer adj (deposit\$6 or epitax\$6) or ALD or ALE) and (metal adj oxide) and (oxygen near5 water)	USPAT; US-PGPUB	2004/05/02 19:42
-	1	("5916365").PN.	USPAT; US-PGPUB	2004/05/02 19:48
-	9387	((nitride adj film) same (silicon with substrate))	USPAT; US-PGPUB	2004/05/02 19:49
-	7214	((nitride adj film) with (silicon with substrate))	USPAT; US-PGPUB	2004/05/02 19:50
-	86733	((atomic adj layer adj (deposit\$6 or epitax\$6)) or \$3CVD	USPAT; US-PGPUB	2004/05/02 19:51
-	2640	((nitride adj film) with (silicon with substrate)) same ((atomic adj layer adj (deposit\$6 or epitax\$6)) or \$3CVD)	USPAT; US-PGPUB	2004/05/02 19:50
-	143	((nitride adj film) with (silicon with substrate) with directly	USPAT; US-PGPUB	2004/05/02 19:58

-	107	((nitride adj film) with (silicon with substrate) with directly) and ((atomic adj layer adj (deposit\$6 or epitax\$6)) or \$3CVD)	USPAT; US-PGPUB	2004/05/02 19:51
-	2198	(atomic adj layer adj (deposit\$6 or epitax\$6))	USPAT; US-PGPUB	2004/05/02 20:27
-	2198	((atomic adj layer adj (deposit\$6 or epitax\$6))) and ((atomic adj layer adj (deposit\$6 or epitax\$6)) or \$3CVD)	USPAT; US-PGPUB	2004/05/02 19:51
-	0	((atomic adj layer adj (deposit\$6 or epitax\$6))) and ((nitride adj film) with (silicon with substrate) with directly)	USPAT; US-PGPUB	2004/05/02 19:51
-	103	(nitride adj film) with (silicon near3 substrate) with directly	USPAT; US-PGPUB	2004/05/02 21:15
-	13	(titanium adj nitride) with (silicon near3 substrate) with directly	USPAT; US-PGPUB	2004/05/02 20:09
-	1	("5406123").PN.	USPAT; US-PGPUB	2004/05/02 20:08
-	2156	(single adj crystal) with nitride	USPAT; US-PGPUB	2004/05/02 20:18
-	1	((atomic adj layer adj (deposit\$6 or epitax\$6))) same ((single adj crystal) with nitride)	USPAT; US-PGPUB	2004/05/02 20:15
-	15	((atomic adj layer adj (deposit\$6 or epitax\$6))) and ((single adj crystal) with nitride)	USPAT; US-PGPUB	2004/05/02 20:14
-	43	(single adj crystal) same ((atomic adj layer adj (deposit\$6 or epitax\$6)))	USPAT; US-PGPUB	2004/05/02 20:18
-	34	(atomic adj layer adj (deposit\$6 or epitax\$6)) and (nitride near2 film) and (precursors same (nitrogen same ammonia))	USPAT; US-PGPUB	2004/05/02 20:47
-	2	lopatin.in. and (purge with nitrogen) and semiconductor and ((atomic adj layer adj (deposit\$6 or epitax\$6))) and nitride	USPAT; US-PGPUB	2004/05/02 20:49
-	1500	lopatin.in. and (purge with nitrogen) ((atomic adj layer adj (deposit\$6 or epitax\$6))) and nitride	USPAT; US-PGPUB	2004/05/02 20:48
-	2	lopatin.in. and (purge with nitrogen) and ((atomic adj layer adj (deposit\$6 or epitax\$6))) and nitride	USPAT; US-PGPUB	2004/05/02 20:48
-	2	lopatin.in. and (purge with nitrogen) and ((atomic adj layer adj (deposit\$6 or epitax\$6)))	USPAT; US-PGPUB	2004/05/02 20:48
-	27	lopatin.in. and ((atomic adj layer adj (deposit\$6 or epitax\$6)))	USPAT; US-PGPUB	2004/05/02 20:48
-	109	(purge with nitrogen) and semiconductor and ((atomic adj layer adj (deposit\$6 or epitax\$6))) and nitride	USPAT; US-PGPUB	2004/05/02 20:51
-	0	(initial\$2 with purge with nitrogen) and ((atomic adj layer adj (deposit\$6 or epitax\$6)))	USPAT; US-PGPUB	2004/05/02 20:56
-	179	initial\$2 with purge with nitrogen	USPAT; US-PGPUB	2004/05/02 20:53
-	39	(initial\$2 with purg\$4) and ((atomic adj layer adj (deposit\$6 or epitax\$6)))	USPAT; US-PGPUB	2004/05/02 20:54
-	2	(("4058430") or ("4413022")).PN.	USPAT; US-PGPUB	2004/05/02 20:56
-	1914	(after adj purging adj3 nitrogen) and ((atomic adj layer adj (deposit\$6 or epitax\$6)))	USPAT; US-PGPUB	2004/05/02 20:56
-	0	(after adj purging adj3 nitrogen) and ((atomic adj layer adj (deposit\$6 or epitax\$6)))	USPAT; US-PGPUB	2004/05/02 20:56
-	1183	after adj purging adj3 nitrogen	USPAT; US-PGPUB	2004/05/02 20:56
-	131	(chamber with purg\$4 with nitrogen) and ((atomic adj layer adj (deposit\$6 or epitax\$6)))	USPAT; US-PGPUB	2004/05/02 20:57
-	120	((atomic adj layer adj (deposit\$6 or epitax\$6) or ALD or ALE) and ("TiCL.sub.4" or (titanium! adj tetrachloride)) and (ammonia! or "NH.sub.3") and (silicon! with substrate))	USPAT; US-PGPUB	2004/05/02 21:04

-	230	((atomic adj layer adj (deposit\$6 or epitax\$6) or ALD or ALE) and ("TiCL.sub.4" or (titanium! adj tetrachloride)) and (ammonia! or "NH.sub.3"))	USPAT; US-PGPUB	2004/05/02 21:05
-	1304	(WBN or WSiN or TiSiN or TaSiN or AlSiN or AlTiN) and ((silicon or semiconductor) with substrate)	USPAT; US-PGPUB	2004/05/02 21:17
-	85	(WBN or WSiN or TiSiN or TaSiN or AlSiN or AlTiN) with ((silicon or semiconductor) with substrate)	USPAT; US-PGPUB	2004/05/02 21:18
-	74	((WBN or WSiN or TiSiN or TaSiN or AlSiN or AlTiN) with ((silicon or semiconductor) with substrate)) and (Substrate with (silicon or Si))	USPAT; US-PGPUB	2004/05/02 21:19